Abstracts

A 10-GHz Amplifier Using an Epitaxial Lift-Off Pseudomorphic HEMT Device

P.G. Young, R.R. Romanofsky, S.A. Alterovitz, R.A. Mena and E.D. Smith. "A 10-GHz Amplifier Using an Epitaxial Lift-Off Pseudomorphic HEMT Device." 1993 Microwave and Guided Wave Letters 3.4 (Apr. 1993 [MGWL]): 107-109.

A process to integrate epitaxial lift-off devices and microstrip circuits has been demonstrated using a pseudomorphic HEMT on an alumina substrate. The circuit was a 10 GHz amplifier with the interconnection between the device and the microstrip circuit being made with photolithographically patterned metal. The measured and modeled response correlated extremely well with a maximum gain of 6.8 dB and a return loss of -14 dB at 10.4 GHz.

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